AMENDMENT TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-20 (Canceled)

Claim 21 (Previously Presented) A mask used for exposing a porous substrate to form a first region and a second region, said first region being filled with a conductive material piercing through the entire thickness of the porous substrate to constitute an interfacial conductive portion, said second region being filled with a conductive material not piercing the entire thickness of the porous substrate to constitute a non-interfacial conductive portion, said mask comprising:

a first light-transmitting region for exposing said first region, and

a second light-transmitting region for exposing said second region,

said second light-transmitting region including an aggregation of fine patterns of which an average aperture ratio is not more than 50% of an average aperture ratio of said first light-transmitting region and

a size of said fine patterns of said second light-transmitting region being in a range of 0.1μm to 10μm.

Claim 22. (Previously Presented) The mask according to claim 21, wherein said fine patterns of said second light-transmitting region are circular or polygonal in configuration, and said fine patterns are arranged in a triangular lattice pattern.

U.S. Serial No. 10/670,520

In reply to Office Action dated: June 28, 2004

Claim 23. (Currently Amended) The mask according to claim 22, wherein said fine patterns of said second light-transmitting region include neighboring circles are circular in configuration, and a center-to-center distance between the neighboring circles is at least twice as large as the diameter of [[said]] each circle.

Claim 24. (Previously Presented) The mask according to claim 21, wherein said fine patterns of said second light-transmitting region are circular or polygonal in configuration, and said fine patterns are arranged to form a square lattice.

Claim 25. (Currently Amended) The mask according to Claim 21, wherein said fine patterns are stripe patterns having an aperture ratio of not more than 50%, and a width between the neighboring stripe patterns is in a range of 0.1 µm to 10 µm.